



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	110mΩ @ V _{GS} = -10V	-4.2A
-60V	130mΩ @ V _{GS} = -4.5V	-3.9A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

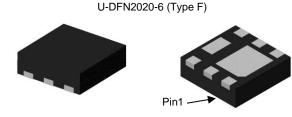
- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features and Benefits

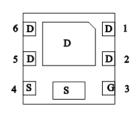
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

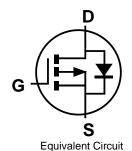
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.007 grams (Approximate) @3







Pin Out Bottom View



Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP6110SFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel		
DMP6110SFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P0 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D	1	Ī	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Units			
Drain-Source Voltage	V _{DSS}	-60	V			
Gate-Source Voltage	V _{GSS}	±20	V			
Continuous Dusin Courset (Note CVV 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l _D	-3.5 -2.8	Α	
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-4.2 -3.4	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-20	А			
Continuous Source-Drain Diode Current (Note 6) $T_A = +25$ °C			Is	-2.1	Α	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-19	А			
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	18	mJ			

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	0	0.76	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	P _D	0.47		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	167	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	$R_{\theta JA}$	121	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	1.97	W	
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	P _D	1.30	V V	
Thermal Peristance Junction to Ambient (Note 6)	Steady State	В	64	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	8		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_		-1	μΑ	V _{DS} = -48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance			_	110	mΩ	V _{GS} = -10V, I _D = -4.5A
Static Drain-Source On-Resistance	R _{DS(ON)}	_		130	11177	$V_{GS} = -4.5V, I_D = -3.5A$
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)	•					
Input Capacitance	C _{ISS}	_	969	_		V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	58	_	pF	
Reverse Transfer Capacitance	C _{RSS}	_	44	_		1.0WH2
Gate Resistance	R _G	_	14	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	8.2	_		
Total Gate Charge (V _{GS} = -10V)	Q _G	_	17.2	_	nC	001/1 404
Gate-Source Charge	Q _{GS}	_	3.0	_	IIC	$V_{DS} = -30V, I_{D} = -12A$
Gate-Drain Charge	Q _{GD}	_	3.1	_		
Turn-On Delay Time	t _{D(ON)}	_	4.4	_		
Turn-On Rise Time	t _R	_	23	_		$V_{GS} = -10V, V_{DS} = -30V, R_{GEN}$
Turn-Off Delay Time	t _{D(OFF)}	_	34	_	ns	$= 6Ω, I_D = -12A$
Turn-Off Fall Time	t _F	_	42	_		
Reverse Recovery Time	t _{RR}	_	13.2	_	ns	$I_S = -12A$, di/dt = -100A/ μ s
Reverse Recovery Charge	Q _{RR}	_	6.2	_	nC	I _S = -12A, di/dt = -100A/μs

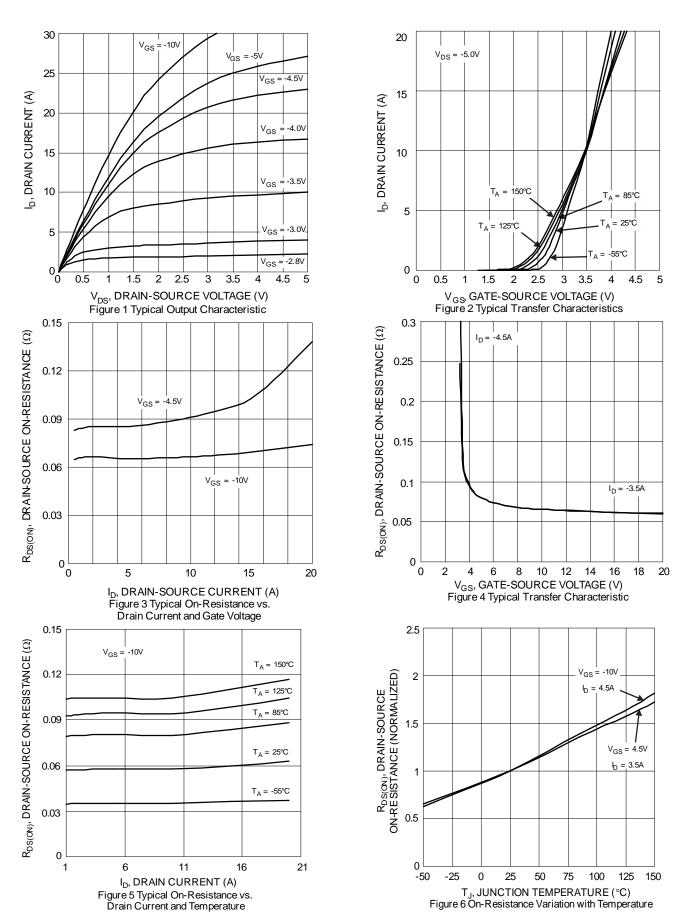
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

^{7.} IAS and EAS rating are based on low frequency and duty cycles to keep $T_J = 25$ °C.

^{8.} Short duration pulse test used to minimize self-heating effect.

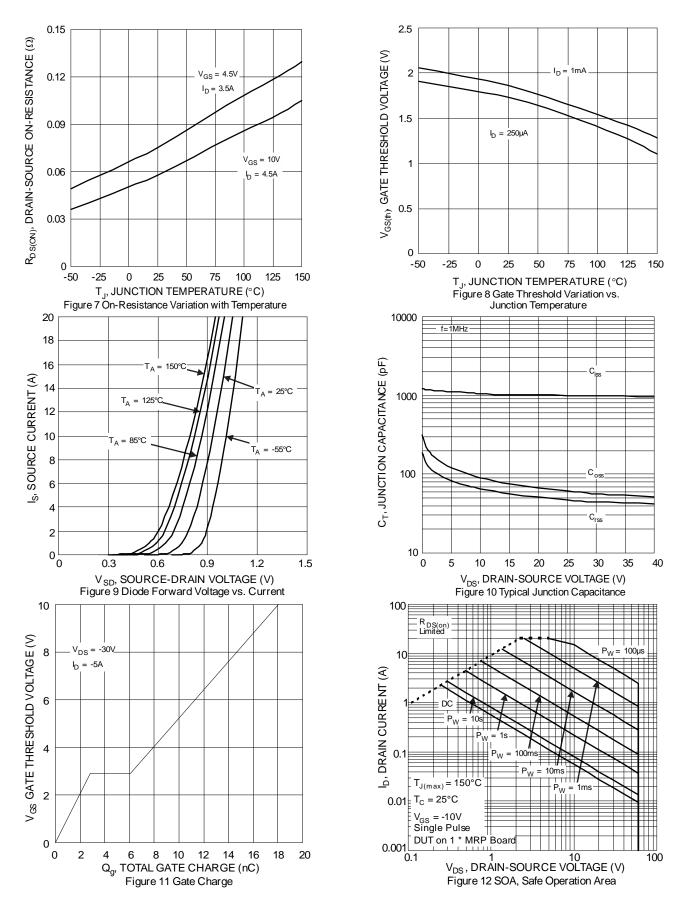
^{9.} Guaranteed by design. Not subject to product testing.



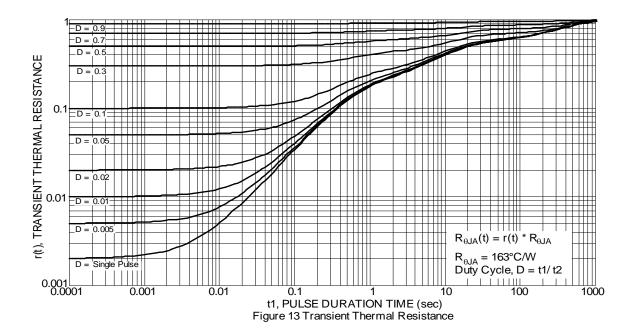


Drain Current and Temperature







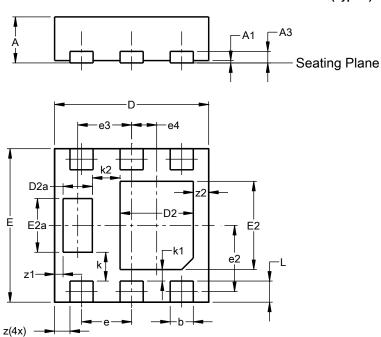




Package Outline Dimension

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

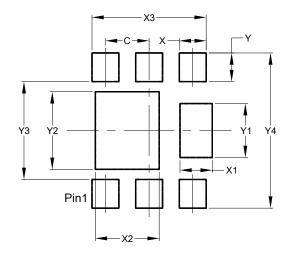


U-DFN2020-6 (Type F)							
Dim	Min Max Typ						
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
е3	0.70 BSC						
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
Z	0.20 BSC						
z 1	0.110 BSC						
z2	0.20 BSC						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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